

ABSTRACT OF THE DISCLOSURE

A semiconductor memory device includes a plate line driving portion having a control transistor connected to a plate line, a selection transistor in which a control electrode is connected to a word line and one end of a main current path is connected to a bit line, a ferroelectric capacitor connected to the other end of the main path of the selection transistor and the plate line, a first power supply connected to a sense amplifier and a precharge circuit, and a second power supply connected to a plate line driving portion, disposed as a separate system from the first power supply and insulated at the time of non-operation from the first power supply. The selection transistor is formed in a first semiconductor region and a main current path of the control transistor is formed in a second semiconductor region that is insulated through insulating films from the first region.